TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

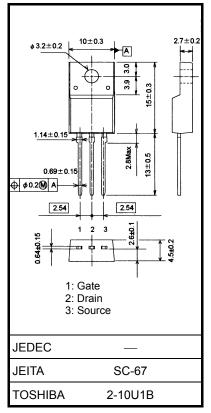
# **TK12A53D**

#### Switching Regulator Applications

- Low drain-source ON-resistance: R<sub>DS</sub> (ON) = 0.5 Ω (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 6.0 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS}$  = 10  $\mu$ A (max) (V<sub>DS</sub> = 525 V)
- Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

# Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	525	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	I <sub>D</sub>	12	А	
	Pulse (Note 1)	I <sub>DP</sub>	48	~	
Drain power dissipation (Tc = $25^{\circ}$ C)		PD	45	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	378	mJ	
Avalanche current		I <sub>AR</sub>	12	А	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	4.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	–55 to 150	°C	



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W

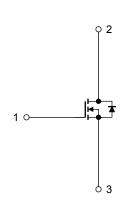
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 4.5 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 12 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.





Start of commercial production 2008-10

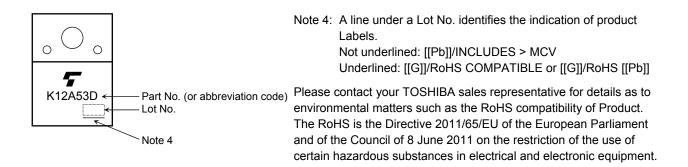
**Electrical Characteristics (Ta = 25°C)** 

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	$V_{GS}=\pm 30~V,~V_{DS}=0~V$		—	±1	μA
Drain cut-off curr	ent	I <sub>DSS</sub>	$V_{DS} = 525 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		_	10	μA
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	525	_	_	V
Gate threshold v	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0	_	4.0	V
Drain-source ON	resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$		0.50	0.58	Ω
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$	1.5	6.0	_	S
Input capacitance		C <sub>iss</sub>			1350	_	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		6	_	pF
Output capacitance		C <sub>oss</sub>			135		
Switching time	Rise time	tr	$I_{0} V$ $I_{D} = 6 A V_{OUT}$		22		
	Turn-on time	t <sub>on</sub>	$\begin{bmatrix} 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 $		55		ns
	Fall time	t <sub>f</sub>	///		15	_	. 113
	Turn-off time	t <sub>off</sub>	Duty $\leq$ 1%, t <sub>W</sub> = 10 $\mu$ s	—	100	_	
Total gate charge		Qg			25		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		16		nC
Gate-drain charge		Q <sub>gd</sub>	]	_	9		

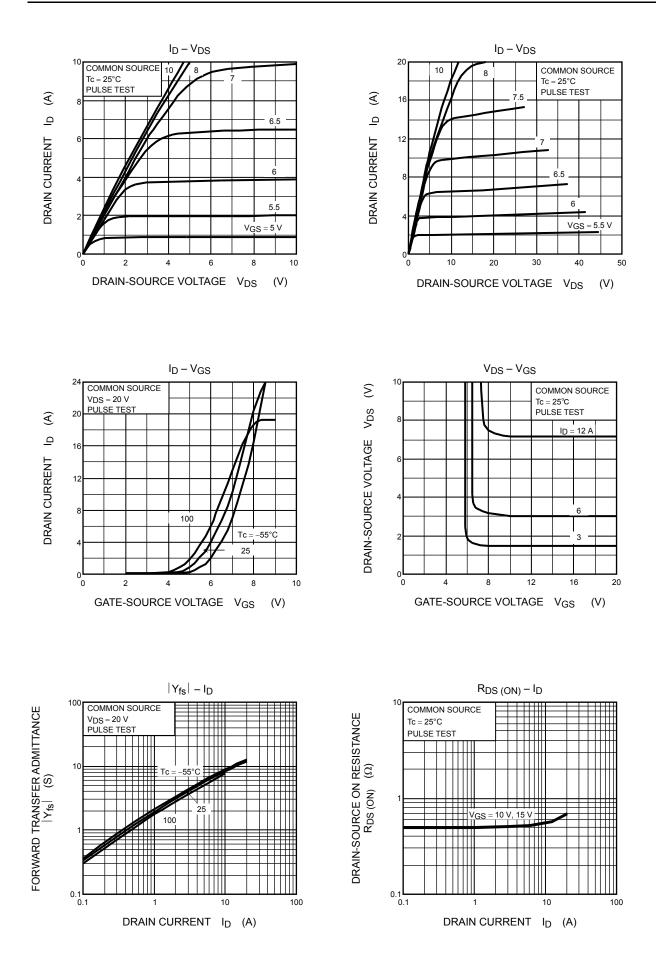
#### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	12	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	48	А
Forward voltage (diode)	V <sub>DSF</sub>	$I_{DR} = 12 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 12 \text{ A}, V_{GS} = 0 \text{ V},$	_	1300	_	ns
Reverse recovery charge	Qrr	dI <sub>DR</sub> /dt = 100 A/μs	_	12	_	μC

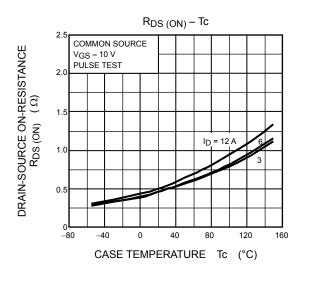
#### Marking

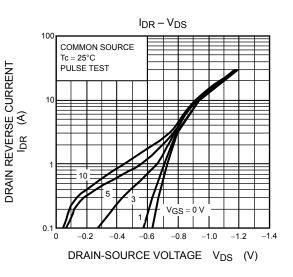


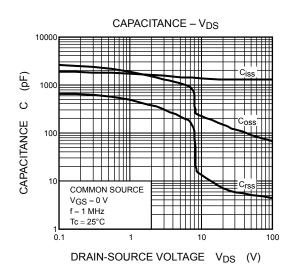
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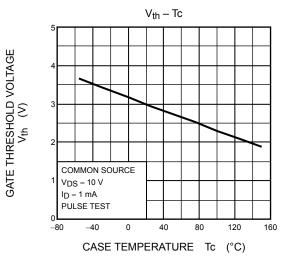


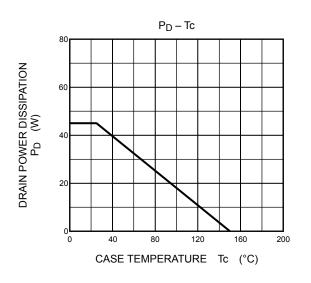
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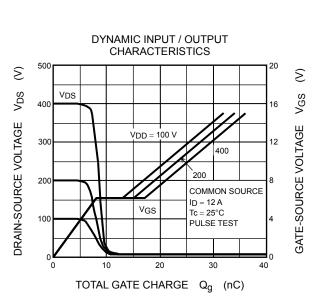


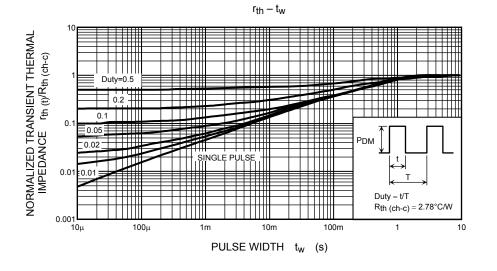




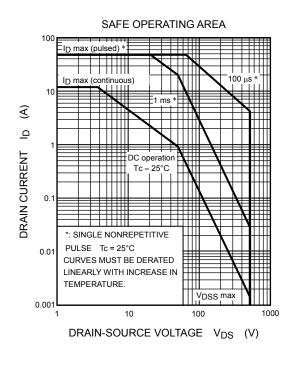


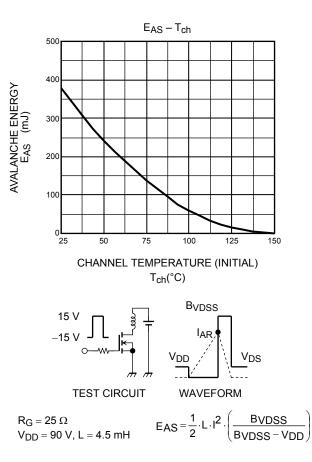






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